

Photo Reflective Sensor

This is a reflective sensor combines a GaA1As infrared light emitting diode with a high sensitive Darlington phototransistor in a mini package.

Features

- Compact
- High performance
- High output
- Easy to mount on PCB
- Widely applicable

Application Ideas

- Timing sensors
- Edge sensors
- Micro floppy disc drivers
- Level sensors of liquid

Specification

Maximum Ratings (Ta=25°C)

Item		Symbol	Rating	Unit
Input	Power Dissipation	PD	100	mW
	Reverse Voltage	VR	5	V
	Forward Current	IF	50	mA
	Pulse Forward current * 1	IFP	1	A
Output	Collector Power Dissipation	Pc	100	mW
	Collector Current	Ic	20	mA
	C-E Voltage	VCEO	30	V
	E-C Voltage	VECO	5	V
Operating Temperature		Topr	-10~+65	°C
Storage Temperature		Tstg	-25~+85	°C
Soldering Temperature *2		Tsol	260	°C

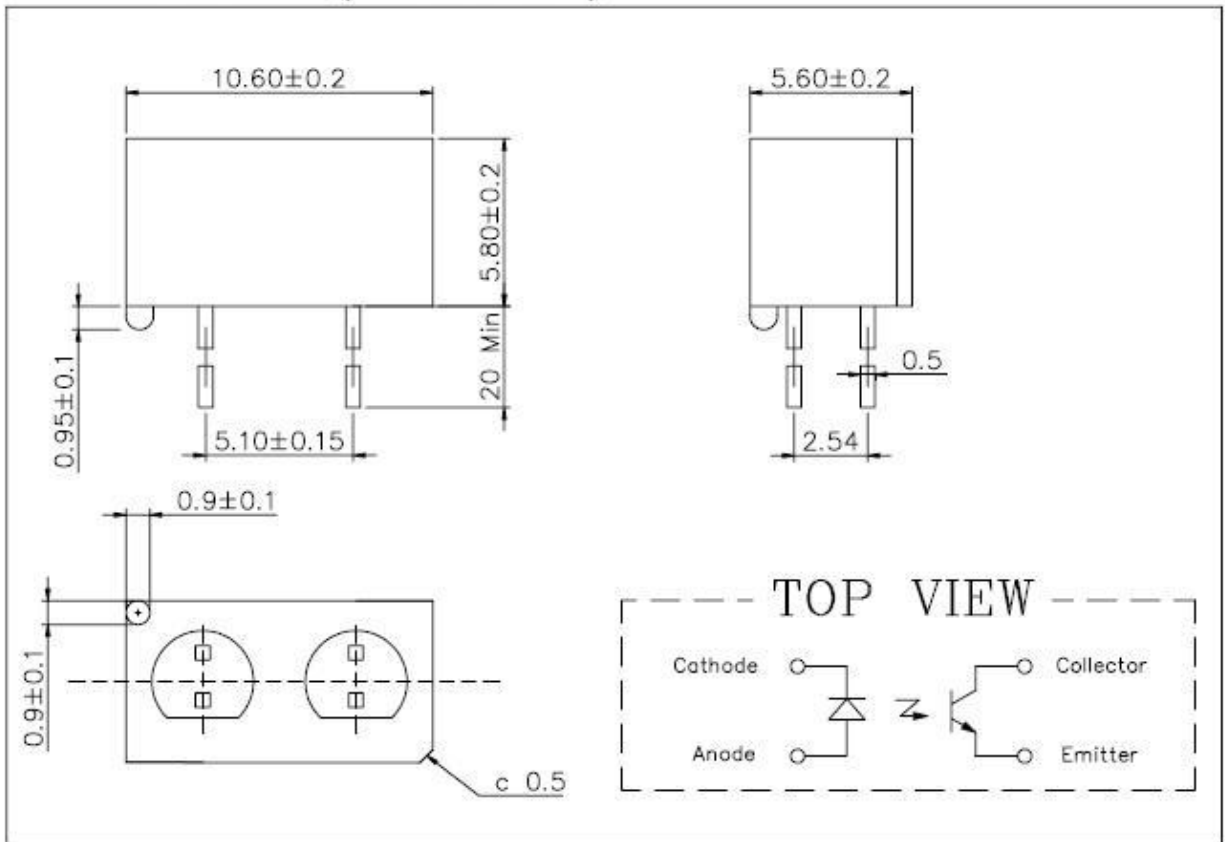
Electro-optical Characteristics (Ta=25°C)

Item		Symbol	Conditions	Min	Typ	Max	Unit
Input	Forward Voltage	VF	IF=20mA		1.2	1.6	V
	Reverse Current	IR	VR=5V			10	μA
	Capacitance	Ct	V=0V, f=1kHz		25		pF
	Peak Wavelength	λP			940		nm
Output	Collector Dark Current	ICEO	VCE=20V			0.1	μA
	Light Current	IL	VCE=5V,IF=20mA	50			μA

	Leakage Current	ICEOD	VCE=5V,IF=10mA			1	μA
Switching Speeds	Rise Time	tr	Vcc=5V, Ic=1mA, RL=1kΩ		15		μsec
	Fall Time	tf			15		μsec

Mechanic Dimensions

Dimensions (Unit: mm)



Tech Support

Please submit any technical issue into our forum.